

BD676A/678A/680A/682

Medium Power Linear and Switching Applications

- Medium Power Darlington TR
- Complement to BD675A, BD677A, BD679A and BD681 respectively



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage : BD676A	- 45	V
	: BD678A	- 60	V
	: BD680A	- 80	V
	: BD682	- 100	V
V _{CEO}	Collector-Emitter Voltage : BD676A	- 45	V
	: BD678A	- 60	V
	: BD680A	- 80	V
	: BD682	- 100	V
V _{EBO}	Emitter-Base Voltage	- 5	V
I _C	Collector Current (DC)	- 4	А
I _{CP}	*Collector Current (Pulse)	- 6	Α
I _B	Base Current	- 100	mA
P _C	Collector Dissipation (T _C =25°C)	14	W
R _{θja}	Thermal Resistance (Junction to Ambient)	88	°C/W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage					
	: BD676A	$I_C = -50 \text{mA}, I_B = 0$	- 45			
	: BD678A		- 60			
	: BD680A		- 80			
	: BD682		- 100			
I _{CBO}	Collector-Base Voltage : BD676A	$V_{CB} = -45V, I_{E} = 0$			- 200	μΑ
	: BD678A	$V_{CB} = -60V, I_{E} = 0$			- 200	μΑ
	: BD680A	$V_{CB} = -80V, I_{E} = 0$			- 200	μΑ
	: BD682	$V_{CB} = -100V, V_{BE} = 0$			- 200	μΑ
I _{CEO}	Collector Cut-off Current : BD676A	$V_{CE} = -45V, V_{BE} = 0$			- 500	μΑ
	: BD678A	$V_{CE} = -60V, V_{BE} = 0$			- 500	μΑ
	: BD680A	$V_{CE} = -80V, V_{BE} = 0$			- 500	μΑ
	: BD682	$V_{CE} = -100V, V_{BE} = 0$			- 500	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 2	mA
h _{FE}	* DC Current Gain : BD676A/678A/680A	$V_{CF} = -3V, I_{C} = -2A$	750			
. –	: BD682	$V_{CE} = -3V, I_{C} = -1.5A$	750			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage					
	: BD676A/678A/680A	$I_C = -2A$, $I_B = -40mA$			- 2.8	V
	: BD682	$I_C = -1.5A$, $I_B = -30mA$			- 2.5	V
V _{BE} (on)	* Base-Emitter On Voltage : BD676A/678A/680A	$V_{CE} = -3V, I_{C} = -2A$			- 2.5	V
	: BD682	$V_{CE} = -3V, I_{C} = -1.5A$			- 2.5	V
* Pulse Test: PW=	300μs, duty Cycle=1.5% Pulse	•		•	•	•

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Typical Characteristics

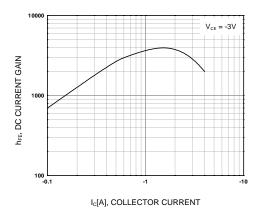


Figure 1. DC current Gain

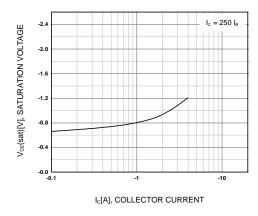


Figure 2. Collector-Emitter Saturation Voltage

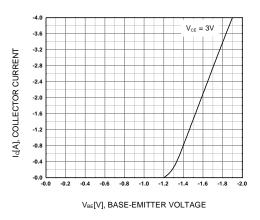


Figure 3. Base-Emitter On Voltage

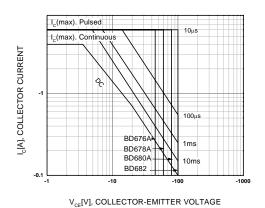


Figure 4. Safe Operating Area

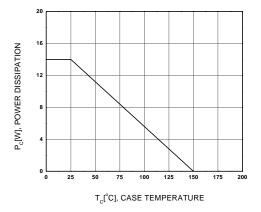
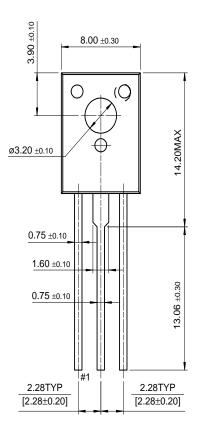


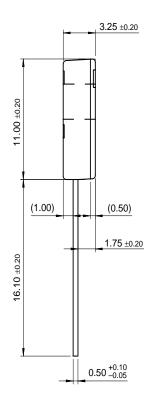
Figure 5. Power Derating

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Package Dimensions

TO-126







Dimensions in Millimeters

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